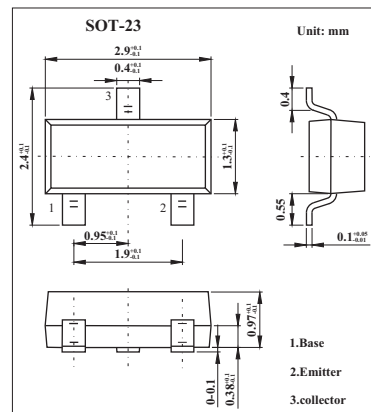


Epitaxial Planar PNP Transistor

KTA1505

Features

Collector Power Dissipation: $P_c=150\text{mW}$ Collector Current: $I_c=500\text{mA}$ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CEO}	-35	V
Collector-Base Voltage	V_{CBO}	-30	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_c	-500	mA
Base Current	I_B	-50	mA
Collector Power Dissipation	P_c	150	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	$^\circ\text{C}$

Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_c=-100\mu\text{A}, I_E=0$	-35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_c=-1\text{mA}, I_B=0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}, I_c=0$	-5			V
Collector Cut-off Current	I_{CBO}	$V_{CB}=-35\text{V}, I_E=0$			-0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=-5\text{V}, I_c=0$			-0.1	μA
DC Current Gain	$h_{FE}(1)$	$V_{CE}=-1\text{V}, I_c=-100\text{mA}$	70		400	
	$h_{FE}(2)$	$V_{CE}=-6\text{V}, I_c=-400\text{mA}$	25			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c=-100\text{mA}, I_B=-10\text{mA}$		-0.1	-0.25	V
Base Emitter Voltage	V_{BE}	$V_{CE}=-1\text{V}, I_c=-100\text{mA}$		-0.8	-1.0	V
Collector Output Capacitance	C_{ob}	$V_{CB}=-6\text{V}, I_E=0, f=1\text{MHz}$		13		pF
Transition Frequency	f_T	$V_{CE}=-6\text{V}, I_c=-20\text{mA}$		200		MHz

 h_{FE} Classification

Marking	AZO	AZY	AZG
Rank	O	Y	GR
h_{FE}	70 140	120 240	200 400